

Methylammonium Tetrafluoroborate Additive for Spontaneous Heterointerface Modulation in a Narrow-Bandgap FAPbI₃ Photoabsorber for Perovskite Solar Cells

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ABSTRACT

Over the past decade, the photovoltaic (PV) performance of perovskite solar cells (PSCs) has been considerably improved with the development of perovskite photoabsorbers. Among these, formamidinium-lead-iodide (FAPbI₃) is a promising photoabsorber owing to its narrow bandgap and is mainly used in n-i-p-structured PSCs. The property modulation of FAPbI₃ photoabsorbers while retaining their narrow bandgap is imperative for further development of PSCs. Molecular tetrafluoroborate anion (BF₄⁻)-based materials can be used as additives in perovskite layers to prevent bandgap widening, while facilitating perovskite crystal growth; thus, they are suitable for FAPbI₃ photoabsorbers in principle. However, BF₄⁻-based additives for narrow-bandgap FAPbI₃ photoabsorbers have not been developed. This is presumably because of the higher temperatures required for FAPbI₃ formation than that for other wide-bandgap perovskites, which likely changes the effects of BF₄-based additives from those for wide-bandgap perovskites. In this study, we verified the applicability of methylammonium tetrafluoroborate (MABF₄) as an additive in narrow-bandgap FAPbI₃ photoabsorbers for improving their PV performance primarily via the spontaneous modulation of the heterointerfaces between FAPbI₃ and carrier-transport materials, rather than through crystal growth facilitation. At the interface of the hole-transport material and FAPbI₃, MABF₄ addition effectively eliminates the surface defects in all FAPbI₃ components, even in the absence of BF₄⁻ anions over the heated FAPbI₃ surface, suggesting a defect-suppression mechanism, which differs from that observed in conventional ones. Moreover, at the interface of FAPbI₃ and the TiO₂ electron-transport material, the BF₄⁻-derived species, which likely includes decomposed BF₄⁻ anions owing to the high-temperature heating, spontaneously segregates upon deposition, thereby modulating the heterointerface. Furthermore, in addition to the carrier mobility ratio in FAPbI₃ (e⁻:h⁺ ≈ 7:3), time-resolved microwave conductivity

measurement revealed that BF_4 addition eliminates carrier traps at the heterointerfaces. Our findings provide insights into the promising FAPbI_3 -based PSCs, offering a valuable tool for their further development.

1. Introduction

Perovskite solar cells (PSCs) have attracted global attention since their first demonstration of power conversion efficiency (PCE) of $\sim 10\%$ with an n-i-p standard structure^{1, 2} and have undergone rapid development in the last decade. PSCs with a standard structure consist of multiple layers: transparent conductive glass/electron transport material (ETM)/perovskite photoabsorber/hole transport material (HTM)/metal electrode (e.g., fluorine-doped tin oxide (FTO) glass/TiO₂/perovskite/Spiro-OMeTAD/Au). Among PSC composites, perovskite photoabsorbers play an important role for achieving high performance.^{3, 4} Perovskite crystals are represented by the ABX_3 structure, comprising organic cations, lead cations (Pb^{2+}), and halide anions at the A , B , and X sites, respectively. The modulation of perovskite crystal composites is a promising strategy for improving the photovoltaic (PV) performance of PSCs.

Among the perovskite composites, formamidinium (FA)-lead-iodide (FAPbI₃) perovskite is promising because their bandgap is relatively close to the ideal single-cell bandgap (≈ 1.4 eV).⁵⁻²⁵ The perovskite crystal quality can be tuned by adding monoatomic ions, such as Cs^+ and Br^- , to the FAPbI₃ perovskite layer.²⁶⁻³⁰ However, these additives increase the perovskite bandgap, thereby limiting the advantages of narrow-bandgap FAPbI₃. The addition of molecular ions can produce effects that cannot be achieved by the addition of monoatomic ions. The molecular tetrafluoroborate anion (BF_4^-) has an ionic radius (2.18 Å) close to that of iodine (2.20 Å) and can act as a substitute for I^- anions in the X -site perovskite.³¹⁻⁴⁶ Furthermore, it has been reported previously that the addition of BF_4^- does not increase the bandgap of wide-bandgap perovskites (e.g., $Cs_{0.2}FAPb(I_{0.8}Br_{0.2})_3$: bandgap ~ 1.62 eV).³³⁻⁴⁶ Therefore, addition of BF_4^- -based materials into the FAPbI₃ perovskite is a promising strategy to retain its narrow bandgap while tuning its properties. However, effective BF_4^- addition to FAPbI₃ perovskites without Cs^+ and/or Br^- has not

yet been developed, which can be ascribed to the limited information on the relevant effects of BF_4^- .

The addition of BF_4^- to the perovskite layers has key effects on the bulk, and thus, this has been studied significantly. For example, BF_4^- -based additives facilitate the crystal growth of wide-bandgap perovskites (e.g., $\text{Cs}_{0.2}\text{FAPb}(\text{I}_{0.8}\text{Br}_{0.2})_3$), enhancing their PV performance by exploiting the improved quality of the perovskite photoabsorber.³³⁻⁴⁶ Meanwhile, since PSCs consist of multiple layers, the heterointerfaces between the perovskite photoabsorber and carrier-transport materials (CTMs, i.e., ETM and HTM) are expected to have a significant impact on PV performance.⁴⁷⁻⁵¹ Even though the effects of BF_4^- addition on PSCs based on wide-bandgap perovskite photoabsorbers have been extensively studied, the effects of BF_4^- addition in the narrow-bandgap FAPbI_3 layer especially on the heterointerfaces have seldom been investigated.

In this study, methylammonium (MA) BF_4 (MABF_4) was added to a narrow-bandgap FAPbI_3 perovskite to improve its PV performance while maintaining its narrow bandgap. To examine the effects of BF_4^- anions, MABF_4 was employed as a representative BF_4^- additive because its counter cation (MA) is same as that of the co-additive of methylammonium chloride (MACl), a vital additive for practical FAPbI_3 crystallization.^{7-12, 23, 52} MABF_4 addition effectively improved the PV performances of FAPbI_3 -based PSCs primarily via enhancement of the heterointerfaces between the FAPbI_3 layer and CTMs, rather than facilitation of the crystal growth of the bulk perovskite (Figure 1). For the HTM/ FAPbI_3 heterointerface, corresponding to outer surface of perovskite layer, MABF_4 addition effectively suppressed the defects of all the FAPbI_3 components presumably via a mechanism, which is different from conventional ones. Meanwhile, regarding the FAPbI_3 /ETM heterointerface, which is underneath the FAPbI_3 layer, compositional depth analysis and time-resolved microwave conductivity (TRMC) measurements revealed the

segregation of BF₄-derived species in the FAPbI₃ layer at the FAPbI₃/ETM interface, which most likely suppressed carrier traps at the interface, leading to extremely long hole-lifetime in the FAPbI₃ layer. Therefore, the obtained insights regarding BF₄-based additives and their effects on narrow-bandgap FAPbI₃, which are different from those for wide-bandgap perovskites, will be a valuable guidance for further development of PSCs.

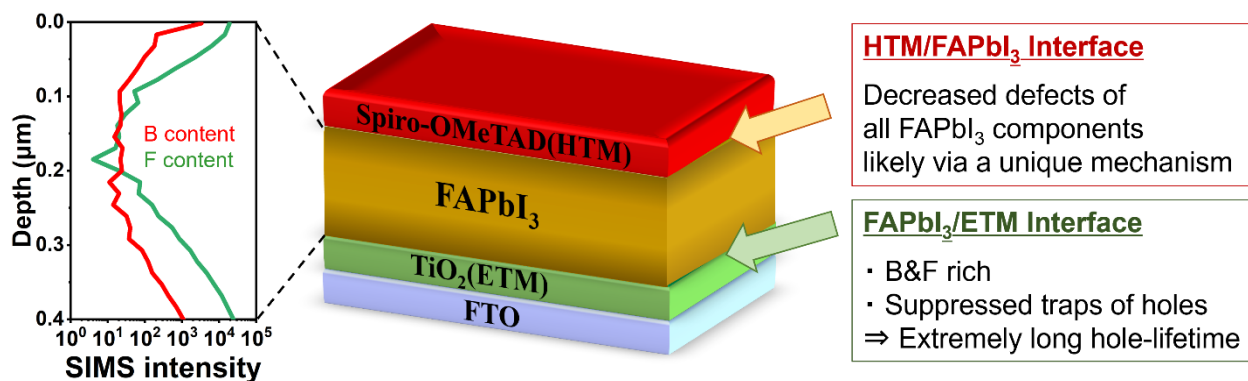


Figure 1. Schematic of MABF₄ addition to FAPbI₃ for heterointerface modulation

2. Experimental Section

FAPbI₃-based PSCs were fabricated using a conventional method^{10, 18-20} with minor modifications (see Supporting Information (SI) for more details). A compact TiO₂ layer was deposited via spray pyrolysis of a titanium diisopropoxide bis(acetylacetonate) ethanol solution over FTO at 450 °C, followed by mesoporous TiO₂ deposition via spin coating. Perovskite precursor solutions were prepared by dissolving 1.8 M FAPbI₃ powder, 0.72 mM MAI, and the desired amount of MABF₄ in a mixed solution of *N,N*-dimethylformamide and dimethyl sulfoxide (4:1, v/v). The perovskite layer was deposited by spin coating the precursor solution at 6000 rpm and 50 s and annealing at 150 °C for 10 min. During spin coating, chlorobenzene (1.0 mL) was added dropwise after 10 s of spinning. A passivation layer was deposited by spin coating a *n*-octylammonium iodide (OAI)

solution (15 mM) over the perovskite layer at 3000 rpm for 30 s and heating at 100 °C for 5 min.⁵³

⁵⁴ Subsequently, HTM was deposited by spin coating a mixture chlorobenzene solution containing spiro-OMeTAD,, 4-*tert*-butylpyridine, lithium bis(trifluoromethanesulfonyl)imide, and FK209 at 4000 rpm for 10 s. Finally, Au was deposited via evaporation.

3. Results and Discussion

The optical absorption spectra of the FAPbI₃ perovskite monolayer samples with and without MABF₄ were measured to investigate the bandgap with BF₄⁻ addition. Figure 2a shows the absorption spectra as a function of the MABF₄ addition. The FAPbI₃ without MABF₄ exhibited a bandgap of 1.54 eV. The bandgap was maintained with the addition of up to 5 mol% MABF₄, whereas it decreased slightly to 1.53 eV with the addition of 10 mol% MABF₄. Therefore, in contrast to Cs⁺ and Br⁻ additives, the addition of MABF₄ to FAPbI₃ did not increase the bandgap rather slightly decreased.

According to previous studies on wide-bandgap perovskites, one of the roles of BF₄⁻-based additives is the facilitation of perovskite crystal growth. Accordingly, the crystal-growth properties of the FAPbI₃ perovskite layer were investigated. Figure S1 shows the X-ray diffraction (XRD) patterns of the perovskite layers with and without MABF₄. A slight change in the XRD peak at around 14°, corresponding to the (110) face was observed among the samples; no peak shifts were observed with up to 5 mol% MABF₄ addition, while a small peak shift from 13.94° to a slightly larger angle (13.96°) was observed with 10 mol% MABF₄ addition (Figure S1b). According to previous studies on the wide-bandgap perovskites, Cs_{0.2}FA_{0.8}Pb(I_{0.8}Br_{0.2})₃ for instance, the replacement of Br⁻ anions with BF₄⁻ anions afforded a shift in the XRD peak due to the substantially smaller ionic radius of the Br⁻ anion (1.96 Å)³ compared to that of the BF₄⁻ anion

(2.18 Å).⁴⁵ The perovskite used in this study is composed of only I⁻ anions (i.e., FAPbI₃), which have an ion radius similar to that of BF₄⁻ (BF₄⁻: 2.18 Å, I⁻: 2.20 Å); therefore, minimal changes were observed in the XRD pattern upon MABF₄ addition. The slight shift in the XRD peak upon addition of 10 mol% MABF₄ can be ascribed to the incorporation of MA cations (2.70 Å) that are smaller than FA cations (2.79 Å).⁵⁵ In terms of δ phase FAPbI₃, which is inactive for the photoabsorber, the MABF₄ addition effectively suppress the formation of the δ phase FAPbI₃ (Figure S1c), which is consistent with the facilitated crystal growth of active FAPbI₃ as will be discussed hereafter.

Although a little changes were observed in the XRD patterns, the morphology varied considerably upon MABF₄ addition. The scanning electron microscopy (SEM) images of the perovskite layers with and without MABF₄ are shown in Figure 2b. The grain size of the perovskite increased with increasing MABF₄ content, indicating that the MABF₄ addition expedited the crystal growth of FAPbI₃. This crystal growth is mainly ascribed to the strong interaction between BF₄⁻ and the lead halide octahedron ([PbX₆]⁴⁻) owing to the high electronegativity and strong electron affinity of BF₄⁻.⁴⁵ Owing to these features, the nucleation of the perovskite crystals was impeded, which in turn expedited their crystal growth.⁴⁵ Larger crystal grains are advantageous for reducing carrier traps, which is beneficial for PV performance.

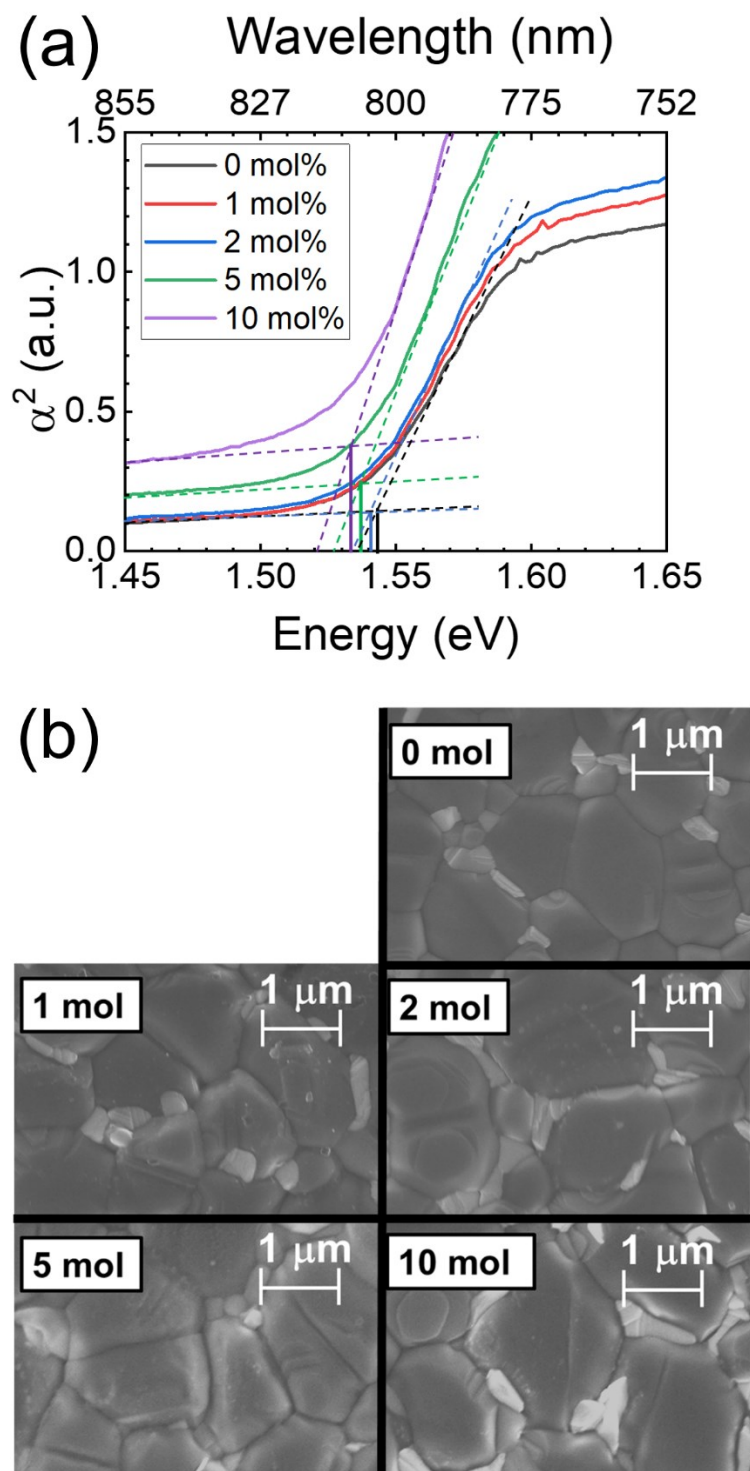


Figure 2. (a) UV–vis absorption spectra and bandgap with different BF_4^- addition amounts. (b)

SEM top-view image of the perovskite films with different amounts of MABF_4 .

MABF₄ addition facilitated crystal growth of the FAPbI₃ perovskite layer. However, the PV parameters of PSCs with MABF₄ addition describe another effect: the modulation of the heterointerfaces between the perovskite layer and CTMs. [Figure 3](#) presents the PV parameters derived from the current density–voltage (J–V) curves of PSCs with and without MABF₄, indicating that optimal MABF₄ addition enhanced the PV performance. [Figure 3a](#) shows distribution of the power conversion efficiency (PCE) obtained under the backward scan. The average PCE under the backward scan ([Table S1](#)) increased from 20.0 ± 1.3% to 21.1 ± 0.9%, 21.6 ± 0.9%, and 21.3 ± 0.7% upon a MABF₄ addition of 1, 2, and 5 mol%, respectively. This PCE increases were mainly owing to the increase in the fill factors (FFs) from 0.70 ± 0.04 to 0.75 ± 0.02, 0.77 ± 0.03, and 0.75 ± 0.02, respectively ([Figure S2 and Table S1](#)). Similarly, in the champion cells ([Table 1](#)), the addition of 1, 2, and 5 mol% MABF₄ increased the PCE from 22.0% to 22.3%, 22.9%, and 22.9%, respectively, under the backward scan. The highest increase in PCE was attributed to the FF enhancement from 0.75 to 0.77, 0.79, and 0.78 with the addition of 1, 2, and 5 mol% MABF₄, respectively. Meanwhile, under the forward scan, MABF₄ addition decreased PCEs in the averages ([Figure S3 and Table S1](#)) and champion cells ([Table 1](#)) owing to a decrease in the open-circuit voltage (V_{oc}). In the champion cells, PCEs decreased from 20.5% without MABF₄ to 18.4% with 2 mol% MABF₄ owing to the decrease in V_{oc} from 1.12 to 1.03 V. Overall, for the J–V curves, the addition of up to 5 mol% MABF₄ enhanced the PCEs of PSCs in the backward scan, however, it also enlarged their hysteresis.

Quasi-steady-state PCEs (QSS-PCEs) were measured for the champion cells to investigate the practical enhancement of PCE upon MABF₄ addition. [Figure 3c](#) shows QSS-PCEs with and without MABF₄. The PSC without MABF₄ exhibited a QSS-PCE of 21.7%, which was similar to the value of the J–V curve under the backward scan. The addition of 1 and 2 mol% MABF₄

increased the QSS-PCE to 22.6% and 22.7%, respectively, which are also similar to the value in the J–V curves under the backward scan, indicating the PV performance enhancement by the MABF₄ addition. In contrast, the QSS-PCE of the PSC with 5 mol% MABF₄ showed an unstable trend and a lower value of 16.6% at 100 s. Similarly, a poor PV performance was determined from the external quantum efficiency (EQE) spectra of the sample with 5 mol% MABF₄ addition. [Figure 3d](#) shows the EQE spectra of PSCs with and without MABF₄. The J_{sc} in the J–V curves of the PSCs with 0 (26.0 mA cm⁻²), 1 mol% (26.3 mA cm⁻²), and 2 mol% (26.2 mA cm⁻²) MABF₄ matched well with the integrated J_{sc} estimated from the EQE curves within 3% (25.2, 25.1, and 25.1 mA cm⁻², respectively). Meanwhile, the samples with 5 mol% MABF₄ achieved low EQE values leading to low integrated J_{sc} (23.3 mA cm⁻²) despite the similar J_{sc} values in the J–V curve to those with 0, 1, and 2 mol% MABF₄, indicating that the sample with 5 mol% MABF₄ deviates from the linearity of the current–excitation intensity relationship.

Overall, the optimal MABF₄ addition (i.e., 1 and 2 mol% addition) enhanced PCE mainly owing to the increase in FF. However, this trend differs from the effects of conventional BF₄⁻-based additives for wide-bandgap perovskites, whereby enhanced PV performance was mainly attributed to the increase in V_{oc} owing to the enhanced quality of the perovskite photoabsorbers with facilitated crystal growth.³¹⁻⁴⁶ In addition to the facilitated crystal growth of FAPbI₃, in the present PSCs, other factors contributed to the enhanced PV performance upon addition of MABF₄ to the FAPbI₃ perovskite. Therefore, the modulation of the heterointerface between the FAPbI₃ perovskite and CTMs with MABF₄ addition and its primary contribution to the PV performance enhancement were examined in this study.

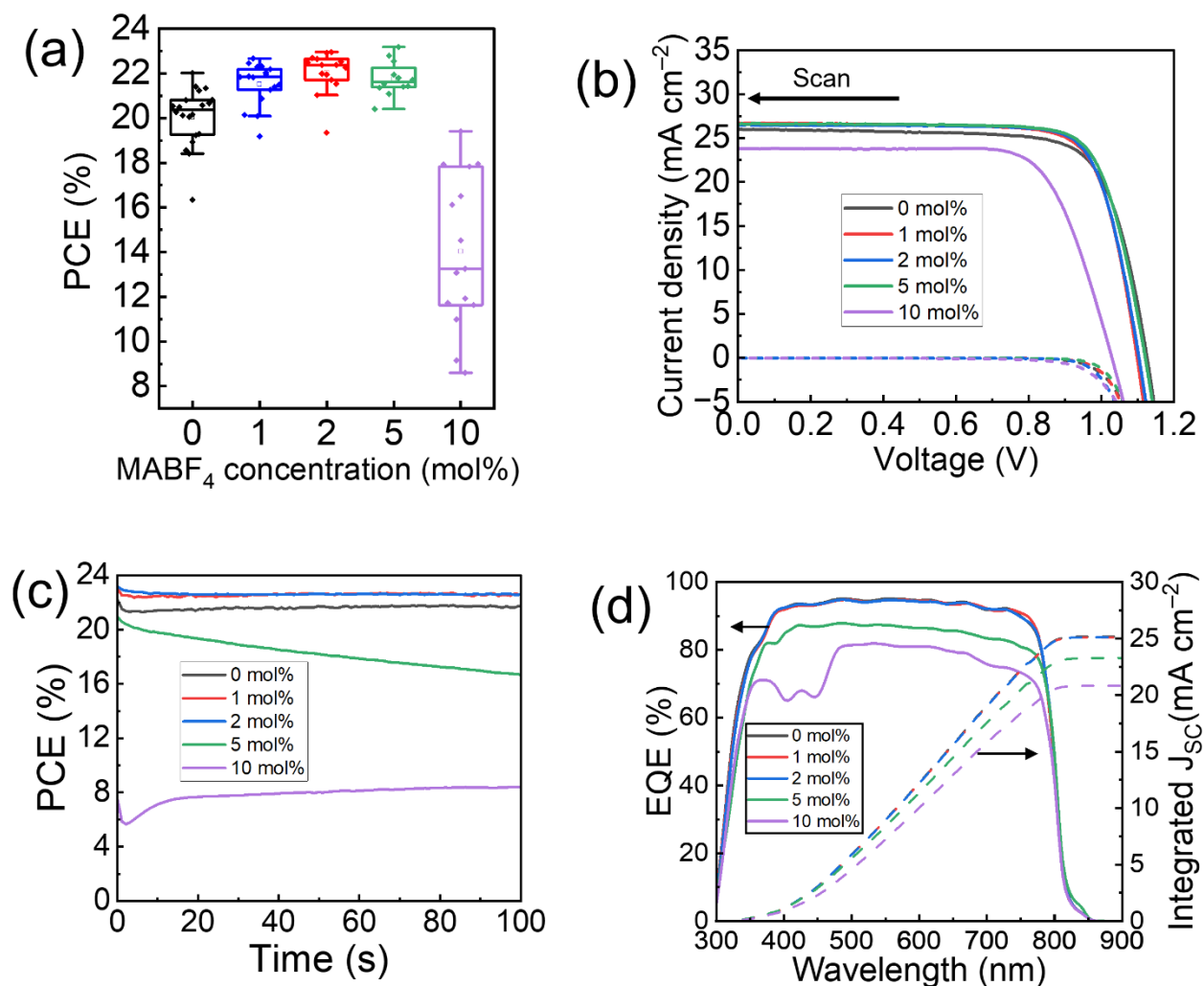


Figure 3. PV performance of PSCs with and without MABF₄: (a) distribution of PCEs in backward scan (corresponding PV parameters: Figure S2 , PV parameters in forward scan: Figure S3); (b) J-V curve with dark (dashed line) in backward scan (forward scan: Figure S4); (c) QSS-PCEs at 0.93, 0.92, 0.92, and 0.80 V for the samples with 0, 1, 2, 5, and 10 mol% MABF₄; and (d) EQE action spectra with integrated J_{sc} (dashed line).

Table 1. PV parameters of champion devices with 0, 1, 2, 5, and 10 mol% MABF₄

MABF ₄ concentration (mol%)	Forward				Backward			
	<i>J</i> _{sc} (mA cm ⁻²)	<i>V</i> _{oc} (V)	FF	PCE (%)	<i>J</i> _{sc} (mA cm ⁻²)	<i>V</i> _{oc} (V)	FF	PCE (%)
0	26.1	1.12	0.70	20.5	26.0	1.13	0.75	22.0
1	26.3	1.07	0.69	19.5	26.3	1.10	0.77	22.3
2	26.2	1.03	0.68	18.4	26.2	1.10	0.79	22.9
5	26.2	1.05	0.66	18.1	26.2	1.12	0.78	22.9
10	25.3	0.87	0.33	7.2	23.8	1.03	0.73	17.9

Regarding heterointerface modulation, we first investigated the HTM/FAPbI₃ interface corresponding to the FAPbI₃ outer surface. Figures 4 and S5 present the X-ray photoelectron spectroscopy (XPS) results of samples with and without MABF₄. In the Pb 4f spectra (Figures 4a), peaks corresponding to Pb²⁺ (at 143 and 138 eV) and Pb⁰ (i.e., the metallic state, at 141 and 137 eV) were observed. An increase in MABF₄ concentration led to a decrease in the intensity of the Pb⁰ (metallic) peaks. Since Pb⁰ acts as a defect and can cause electron leaking, its decrease presumably contributed to the enhancement of the observed PV performance. Figure S5a shows a slight high-energy shift of the Pb²⁺ peaks from 143.1 to 143.3 eV with the addition of MABF₄. The formation of anion defects from Pb weakens the coordination between Pb and halogens and thereby results in a low-energy shift. Therefore, the observed high-energy shift indicates that the defects of anion coordinating to Pb²⁺ were effectively eliminated by the added MABF₄, contributing to the observed improvement in PV performance.

Apart from Pb, XPS of the other perovskite composites (i.e., C, N, and I) did not exhibit any peak shifts (Figure S5b-d). However, their surface compositions also indicated mitigation of surface defects upon MABF₄ addition. The I/Pb composition ratios of the I anion are presented in Figure 4b. An increase in the added amount of MABF₄ from 0 to 10 mol% gradually increased the I/Pb ratios from 1.3 to 1.8, and consequently, decreased the difference between the experimental and theoretical values (3.0). This trend suggests that MABF₄ addition contributed to the decrease in the iodine defect density, which is consistent with the high-energy shift of the Pb²⁺ peaks with MABF₄ addition (Figure S5a).

Figures 4c and 4d present the experimental and theoretical composition ratios of C/Pb and N/Pb, respectively, for the A-site perovskite composites. Without MABF₄ addition, the measured C/Pb (0.3), N/Pb (0.3), and N/C (0.9) ratios differed significantly from their corresponding theoretical values of 1.0, 2.0, and 2.0, respectively. However, the addition of MABF₄ increased the C/Pb ratio from 0.2 to 0.4, approaching the theoretical value of 1.0, and raised the N/Pb ratio from 0.3 to 0.5, nearing the theoretical value of 2.0. These increases suggest a mitigation of the perovskite A-site cation defects. Figure 4e shows the experimental and theoretical N/C composition ratios. For FA, the experimental ratio is close to the theoretical value of 2.0, indicating that over the perovskite surface, the amount of FA exceeds that of MA, which originated from MAI and MABF₄. Notably, the addition of MABF₄ raised the N/C ratio from 0.9 to 1.5, approaching the theoretical value for FA (2.0) and surpassing that for MA (1.0). These results demonstrate that MABF₄ addition effectively suppressed the surface defects of FA on the FAPbI₃ surface. This decreased FA defect presumably contributed to the optical bandgap shift of FAPbI₃ to the slightly narrower one observed in Figure 2a, as estimated by a theoretical study⁴¹. Consequently, optimal MABF₄ addition reduced the defects generated from all the FAPbI₃

compositions, including FA cations, Pb^{2+} cations, and I^- halogens. This phenomenon is advantageous for both effective hole collection and prevention of electron leakage, leading to the enhancement of PV performance.

The perovskite surfaces were examined regarding BF_4 anion compositions to investigate their defect suppression mechanism, and the absence of BF_4 species on the perovskite surface was revealed. [Figure S5e](#) presents the XPS profile of F 1s; fluorine peaks were not observed with the addition of 1–5 mol% MABF_4 , whereas the addition of 10 mol% MABF_4 resulted in a small peak at 684 eV. [Figure S5f](#) shows the XPS profile of B 1s; boron peaks (189 eV) were absent in the spectra of all samples. We here note that the peaks at 186 and 198 eV in [Figure S5f](#) derived from I 4s and Cl 2p, respectively, meaning that no boron was detected. Therefore, the BF_4 species most likely disappeared from the perovskite surface during the heating process of the perovskite layer. This trend differs from previously reported ones regarding other types of perovskites (e.g., $\text{Cs}_{0.2}\text{FAPb}(\text{I}_{0.8}\text{Br}_{0.2})_3$), which require lower heating temperatures around 373 K, more suitable for p-i-n inverse structured PSCs, compared to FAPbI_3 (423 K; mostly used in n-i-p structure PSCs as in the present study). Consequently, the disappearance of BF_4 species from the perovskite surface may be attributed to the high heating temperatures applied. Previous studies on BF_4 addition to wide-bandgap perovskites^{39, 45} and a theoretical estimation for FAPbI_3 perovskite⁴¹ revealed that co-existing BF_4 anions on the perovskite surface stabilize FA and/or MA cations due to the strong electronegativity of the BF_4 anion. Thus, according to the literatures, the presence of BF_4 on a perovskite surface is vital for achieving this effect.^{39, 41, 45} However, in the present system, the BF_4 anions disappeared from the perovskite surface during the post-heating process, yet MABF_4 addition to FAPbI_3 effectively suppressed defect formation. Hence, the mechanism for defect

suppression in this study presumably differs from that observed in conventional cases of BF_4 addition.

To investigate the defect suppression mechanism in the present system and assess the defect formation mechanism of FAPbI_3 , XPS analysis of samples with BF_4 addition subjected to heating for various durations was conducted (Figure S6 and S7). The sample without heating exhibited an F 1s peak at 683 eV (Figure S6), corresponding to BF_4 . However, with only 1 min of heating, the F 1s peak disappeared, suggesting that the BF_4 anion either evaporated or migrated to the underside during the initial stage of heating. Consequently, BF_4 anions were absent from the perovskite surface for most of the heating duration, though this BF_4 addition was effective in preventing defect formation (Figure 4). Indeed, the ratios of other components on the perovskite surface remained almost steady after heating for 1 min (Figure S7). These results suggest that BF_4 addition primarily affects the formation of crystal nuclei at the initial stage of perovskite layer formation. Compared to ions in rigid bulky crystals, nucleated ions generally move more easily; in other words, the crystalline nuclei are prone to form defects. Therefore, the addition of MABF_4 presumably suppresses the formation of defect nuclei and, eventually, the overall defect formation on the FAPbI_3 perovskite surface. Such findings also imply that for achieving high-quality FAPbI_3 , which requires relatively high-temperature heating, controlling the nucleus states and suppressing the formation of defective crystal nuclei can be essential.

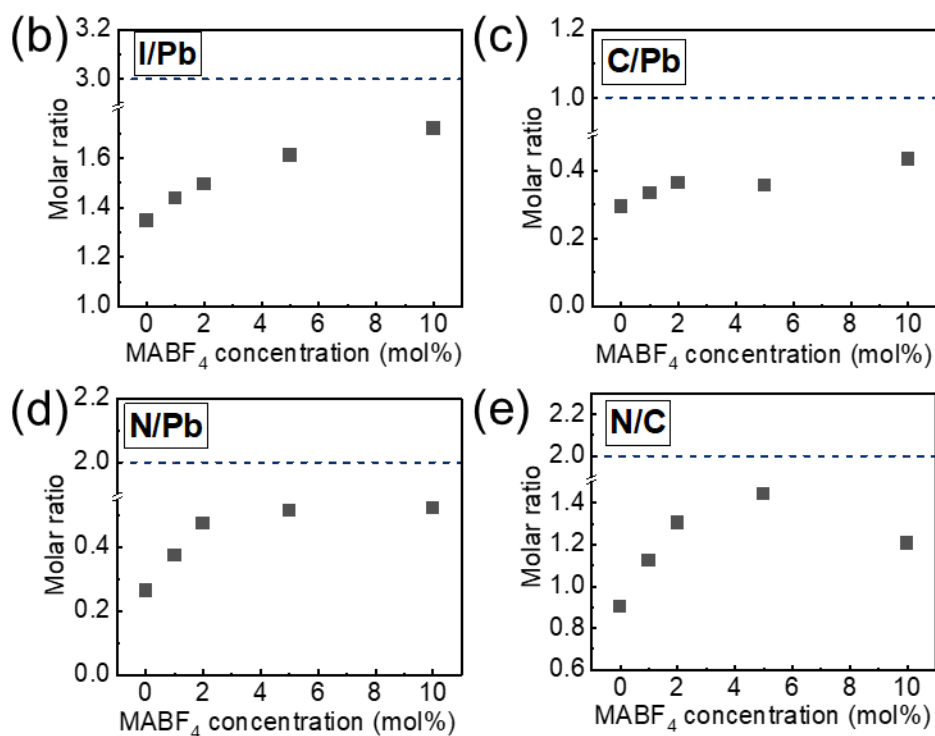
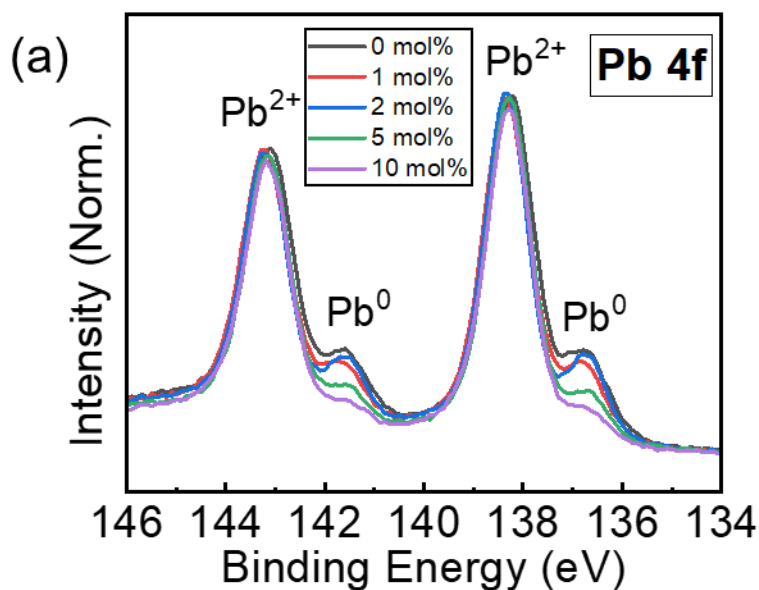


Figure 4. (a) XPS Pb 4f profile of the FAPbI₃ films with various amounts of MABF₄, estimated surface molar ratios of the samples (b) C/Pb, (c) N/Pb, (d) N/C, and (e) I/Pb (dashed line: theoretical values).

Apart from the HTM/FAPbI₃ interface, the effects of MABF₄ addition on the underlying FAPbI₃/ETM heterointerface were also investigated. To analyze the underlying FAPbI₃/ETM heterointerface, a compositional depth analysis was conducted. Figure 5 shows the secondary-ion mass spectrometry (SIMS) result of the samples with and without MABF₄. To detect F and B ions, SIMS analyses of the negative and positive ions were performed, respectively. The perovskite, TiO₂, and FTO regions were differentiated according to the Pb, Ti, and Sn concentrations at depths of 30 cycles (perovskite), 80 cycles (TiO₂), and 170 cycles (FTO) (see experimental section in SI for the determination of each regime). The negative ions in the sample without BF₄⁻ (Figures 5a) at a depth of 22 cycles exhibited a sharp increase and saturated F content, which might be ascribed to the F originating from FTO. However, the F component trend of the sample containing MABF₄ was different from that of the sample without MABF₄; unlike the sample without MABF₄, F was present in the perovskite bulk and exhibited compositional gradation. In the vicinity of the perovskite surface, an F signal (approximately 10000 counts) was detected. We here note that BF₄⁻ was absent in the outermost layer (a few nanometers depth) of the FAPbI₃ perovskite, as detected by XPS. In contrast, SIMS analysis detected BF₄⁻ species in FAPbI₃ perovskite surface, but SIMS is estimated to have a depth resolution of several tens of nanometers, much deeper than that of XPS. Furthermore, the F signal counts decreased from 1000 to 10 as the depth was increased from 0 to 10 cycles. Subsequently, it steeply increased from 10 and saturated at over 10000 counts at a depth of 10 cycles, which was shallower than that of the sample without MABF₄ addition and thus could not be attributed to FTO. Accordingly, MABF₄ addition led to F compositional gradation; high F concentrations were observed in the vicinity of the perovskite surface and the FAPbI₃/TiO₂ interface. The positive-ion SIMS results for B exhibited similar trends to those of F observed in

the negative-ion SIMS results. For the sample with MABF₄ addition, the B signal count decreased from 1000 to 20 as the depth increased from 0 to 20 cycles, and then sharply increased from 10 to 10,000 as the depth increased from 10 to 40 cycles; notably, large counts were obtained for samples with broad perovskite/TiO₂ interfaces. In contrast, the sample without MABF₄ addition exhibited a considerably weaker B signal than the sample with BF₄⁻. Thus, both B and F were detected at the same depth (10 cycles) and exhibited similar trends, which could be attributed to BF₄⁻ anions. Further investigations were conducted by time-of-flight (ToF)-SIMS analyses, which can detect the depth profiles of molecular ions. Negative-ion detection mode, which sensitively detects ions that easily become negatively charged, was employed for the ToF-SIMS measurement to detect BF₄⁻ anions. [Figure S8](#) shows the depth profiles of the samples with and without 2 mol% MABF₄. Although the presence of F (*M* = 19) was clearly observed, a little BF₄ (*M* = 87) was also detected. This result suggests that some of the BF₄ anions were decomposed, likely because of the relatively high-temperature heating of the FAPbI₃ layer in the deposition process. [Figure S9](#) presents the integrated mass spectra corresponding to F (*M* = 19) and BF₄ (*M* = 87) anions at all depths of the FAPbI₃ layer, excluding the FTO regime (2–35 cycles in [Figure S8](#)). The integrated intensity of BF₄ in the FAPbI₃ sample with MABF₄ addition was clearly observed to be around 3 ([Figure S9a](#)), confirming the presence of BF₄ anion in the FAPbI₃ layer. Meanwhile, integrated intensity of F was approximately 40, ten-times larger ([Figure S9b](#)). Although the BF₄ should be easily become negative ions, the detected intensity was significantly smaller than F. Thus, the detected F was most likely derived from the fragmentation of the BF₄ anion and decomposed BF₄-based species. We here note that the integrated intensities of BF₄ and F in the FAPbI₃ sample without MABF₄ addition were negligible, and hence, the detected BF₄ and F were originated from MABF₄ addition. Therefore, the presence of BF₄⁻ in the FAPbI₃ layer was confirmed from the integrated mass

spectrum, but the decomposition of the BF_4^- in the FAPbI_3 layer was also suggested. Consequently, the species derived from the BF_4^- anions segregated in the vicinity of the surface of the perovskite layer and, notably, at the $\text{FAPbI}_3/\text{TiO}_2$ interface; the addition of MABF_4 to the FAPbI_3 photoabsorber spontaneously modulated the perovskite bulk composition and $\text{FAPbI}_3/\text{TiO}_2$ heterointerface. Although a fraction of the BF_4^- anions most likely decomposed, the spontaneous modulation of the $\text{FAPbI}_3/\text{ETM}$ heterointerface was beneficial in terms of carrier dynamics and stability against humidity as discussed later.

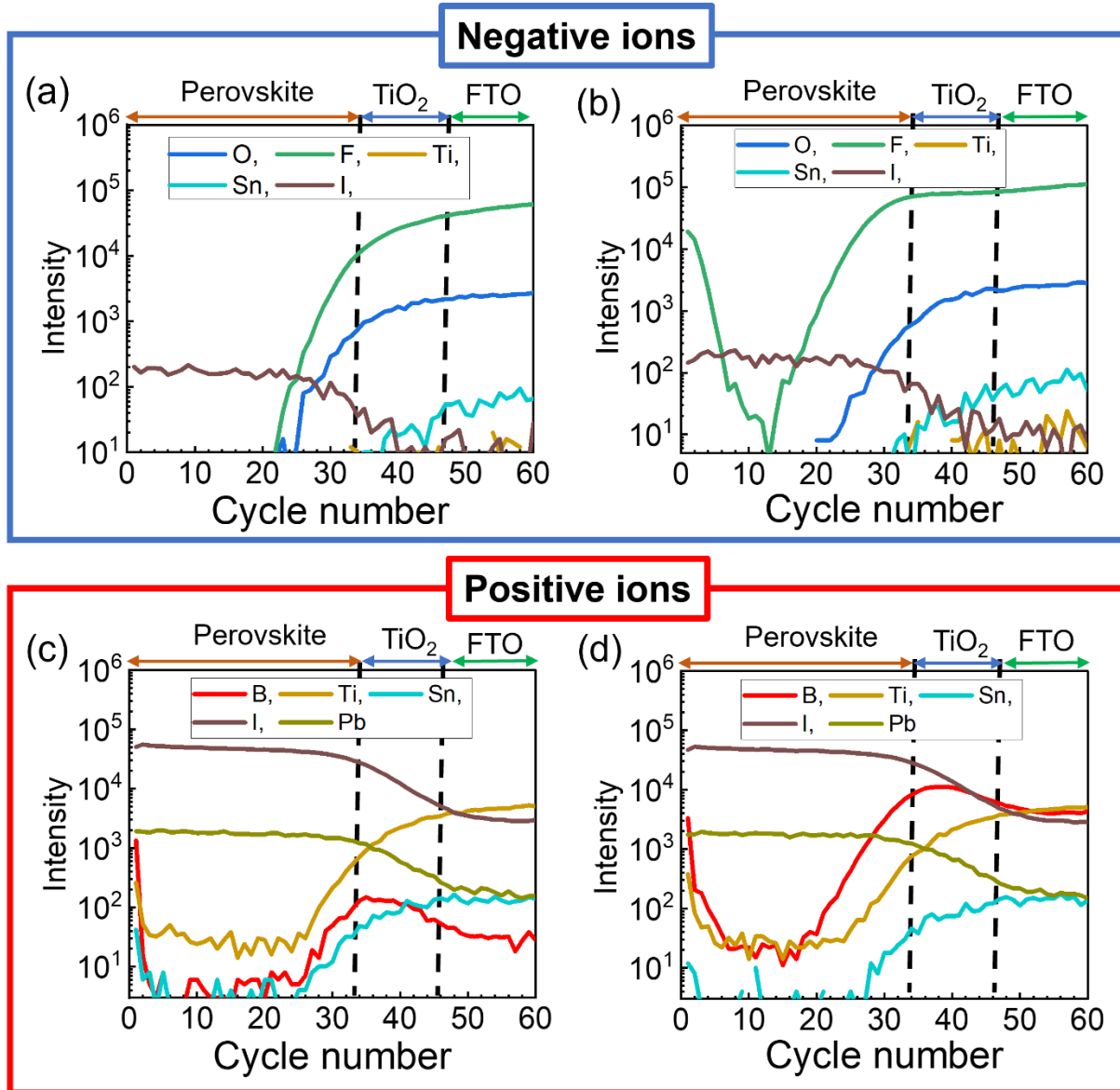


Figure 5. SIMS profiles and negative-ion defects: (a) without MABF₄, (b) with MABF₄ and positive ions, (c) without MABF₄, and (d) with MABF₄.

Examining the effects of this spontaneous modulation on the carrier dynamics is crucial to understand their contribution to the PV performance. TRMC measurements^{19, 20, 56-62} are reportedly effective for investigating the carrier trapping ability of the heterointerface between the perovskite and CTMs in PSCs without removing CTMs. Because the carrier mobility in CTMs is significantly lower than that in perovskites, TRMC measurements are performed to determine the lifetime of the carriers remaining in the perovskite after carrier injection from the perovskite to a CTM. Thus, TRMC decay indicates changes in the electron trapping efficiency at the perovskite/CTM heterointerface (see SI for more details).

Prior to analyzing the CTM/FAPbI₃ heterointerfacial characteristics, TRMC measurements were conducted on the FAPbI₃ monolayer samples with and without MABF₄ addition. [Figure S10a](#) shows the TRMC decay of the FAPbI₃ monolayer samples with and without MABF₄ addition, and [Figure 7a and Table S2](#) presents their TRMC lifetimes estimated via single exponential curve fitting. Regarding the TRMC measurements, a weak excitation of 0.6 nJ cm⁻² per pulse was employed, sufficient to suppress the TRMC decay facilitated by high carrier concentration²⁰ ([Figure S11](#)). As the MABF₄ concentration increased from 0 to 1 mol%, the TRMC lifetime extended from 22.1 ± 0.3 to 54.1 ± 0.9 μs. A further increase in the MABF₄ concentration resulted in a slight decrease in the TRMC lifetime (e.g., with 2 and 10 mol% addition, the lifetime decreased to 43.0 ± 0.5 and 38.2 ± 0.4 μs, respectively); however, this shortened lifetime still surpassed that observed without MABF₄ addition. This extension of carrier lifetimes in the FAPbI₃ monolayer sample can be primarily attributed to the improved interface of the FAPbI₃ perovskite and the quartz substrate as elucidated previously, in addition to the crystal growth facilitation observed in the SEM images ([Figure 2b](#)). Furthermore, the small decreases in the TRMC lifetimes upon excess

addition of MABF₄ suggest that excess MABF₄ addition can be detrimental to the quality of the perovskite layers perhaps due to the presence of decomposed BF₄ species.

The carrier injection characteristics and relative carrier mobilities were investigated via comparisons of the TRMC decay of the FAPbI₃ monolayer and CTM/FAPbI₃ bilayer samples within a short time scale (~1500 ns). Figures 6a and 6b present the TRMC signals of the samples with and without MABF₄ addition, respectively, for (i) FAPbI₃ perovskite monolayer, (ii) FAPbI₃/ETM bilayer, and (iii) HTM/FAPbI₃ bilayer samples. The TRMC signal intensities of the bilayer samples were normalized relative to that of the FAPbI₃ monolayer samples. Both types of samples with and without MABF₄ exhibited similar trends. The TRMC signals of the FAPbI₃ monolayer samples (black lines in Figures 6a and 6b) were almost steady within this time scale. The TRMC signal of the FAPbI₃/ETM bilayer (red lines in Figures 6a and b) gradually decreased up to approximately 500 ns and then became almost steady with an intensity of approximately 0.3 relative to that of the FAPbI₃ monolayer sample; therefore, the initial decay most likely represented the electron injection from FAPbI₃ to TiO₂ ETM. The HTM/FAPbI₃ bilayer sample (blue lines in Figures 6a and 6b) exhibited an initial signal intensity of 0.7 relative to that of the monolayer sample; subsequently, this signal intensity remained steady, suggesting that the hole injection from FAPbI₃ to the HTM was almost completed within the time resolution of the TRMC measurement. The estimated sum of the TRMC signal intensities of the FAPbI₃/ETM bilayer and that of the HTM/FAPbI₃ bilayers are also shown in Figures 6a and 6b as green dots. These results indicate that the sum of the TRMC intensities after the signal becomes steady (~500 ns) is approximately 1.0, which is the same as that of the FAPbI₃ monolayer sample. Therefore, this matching between the TRMC intensity of the monolayer and the sum value supports the aforementioned discussion; the initial signal decay shown by the FAPbI₃/ETM sample represents electron injection, and the

initially reduced signal intensity of the HTM/FAPbI₃ sample demonstrates that the hole injection is faster than the time resolution of the TRMC measurement. Thus, in the present system, the hole injection from FAPbI₃ to the HTM is significantly faster than the electron injection from FAPbI₃ to the ETM.

Such findings shed light on the carrier mobilities of the FAPbI₃ photoabsorber; the estimated carrier mobility ratio of FAPbI₃ between electrons (e⁻) and holes (h⁺) is approximately 7:3 for e⁻:h⁺. Although the mobilities of electrons and holes in perovskites are considered to be almost equal, it is revealed that in the case of the present FAPbI₃, the electron mobility is much higher than the hole mobility by approximately twofold.

To investigate the characteristics of the HTM/FAPbI₃ heterointerface, the TRMC signal decay of the HTM/FAPbI₃ bilayer samples was investigated (Figure 6c and Figure 7b). Hole injection was completed within the time resolution of the measurement, therefore, the TRMC decays of the HTM/FAPbI₃ bilayer samples represent the electron lifetime in the FAPbI₃ layer in the presence of the HTM/FAPbI₃ heterointerface ($\tau_{HTM/FAPbI_3}$). The TRMC lifetime of the sample without MABF₄ addition was $\tau = 6.7 \pm 0.1 \mu\text{s}$, which is considerably shorter than that of the monolayer sample (Figure 7b and Table S2), indicating that the HTM/FAPbI₃ heterointerface acts as a significant carrier trap. The TRMC lifetimes remained almost unchanged with the addition of MABF₄ up to 2 mol% (1 mol%: $\tau = 8.7 \pm 0.1 \mu\text{s}$, 2 mol%: $\tau = 7.6 \pm 0.1 \mu\text{s}$), whereas they increased to $15.7 \pm 0.2 \mu\text{s}$ and $12.3 \pm 0.2 \mu\text{s}$ when 5 and 10 mol% of MABF₄ were added, respectively (Figure 7b and Table S2). However, even with MABF₄ addition, the TRMC decays of the HTM/FAPbI₃ bilayer samples were substantially shorter than those of the perovskite monolayer samples, strongly suggesting the formation of carrier traps at the HTM/FAPbI₃ heterointerface during the HTM deposition process. These carrier traps were presumably suppressed by MABF₄

as the TRMC lifetimes of the HTM/FAPbI₃ bilayer samples were extended. However, they remained even upon MABF₄ addition as represented by the shorter TRMC lifetimes of the HTM/FAPbI₃ samples compared to the corresponding FAPbI₃ monolayer samples.

Compared to the HTM/FAPbI₃ bilayer samples, the FAPbI₃/ETM bilayer samples exhibited a different trend. The TRMC signal of FAPbI₃/ETM in a short range (~1500 ns) is shown in [Figure S10b](#). These TRMC decays represent both the electron injection from FAPbI₃ to ETM in the initial stage and the lifetime of the hole in FAPbI₃ ($\tau_{FAPbI_3/ETM}$). Regarding the former characteristic, the TRMC lifetime attributed to electron injection ($\tau_{e- inject}$) was estimated and is presented in [Figure 7c](#) and [Table S2](#) (see SI for estimation details). The $\tau_{e- inject}$ slightly increased from 86 ns to 220 ns with an increase in the MABF₄ concentration to 2 mol%. Further addition of MABF₄ to 5 and 10 mol% increased the $\tau_{e- inject}$ to 460 ns and 1566 ns, respectively. This increase in the $\tau_{e- inject}$ upon MABF₄ addition suggests that the accumulated BF₄-derived species around the FAPbI₃/TiO₂ interface may hamper electron injection from FAPbI₃ to TiO₂.

However, the accumulated BF₄ composite is presumably beneficial in suppressing carrier traps; after completion of the electron injection (i.e., after several μ s), the TRMC decays correspond to the hole lifetimes in perovskite, while MABF₄ addition extended the TRMC lifetimes. [Figure 6d](#) and [Figure 7d](#) presents the TRMC decays of the FAPbI₃/ETM samples in a long-time range, and the hole-lifetimes corresponding to TRMC lifetime of these sample were estimated ([Table S2](#)). The FAPbI₃/ETM sample without MABF₄ addition exhibited a TRMC lifetime of $\tau = 221 \pm 12 \mu$ s, which is considerably longer than that of the monolayer FAPbI₃ ($\tau = 22.1 \pm 0.3 \mu$ s). This is presumably owing to the physically separated electrons and holes decreasing the recombination frequency, suggesting that the formed carrier traps at the FAPbI₃/ETM interface are substantially less than those at the HTM/FAPbI₃ interface ($\tau = 6.7 \pm 0.1 \mu$ s). Meanwhile, with

an increase in MABF₄ addition from 0 to 1 and 2 mol%, the TRMC lifetime increased from 221 ± 12 to 266 ± 18 and 374 ± 32 μs, respectively. Further increase in MABF₄ addition to 10 mol% extended the TRMC lifetime to 516 ± 58 μs.

Consequently, optimal MABF₄ addition led to the extension of carrier lifetimes in the FAPbI₃ in the presence of heterointerfaces with CTMs, strongly suggesting suppression of carrier traps formation at the heterointerfaces. In particular, the hole lifetime in FAPbI₃ in the presence of the FAPbI₃/ETM heterointerface could be extended up to 516 ± 58 μs, which is extremely long. Thus, the decreased carrier traps presumably contributed to the enhancement of PV performance. However, excess MABF₄ addition inhibited electron injection from the FAPbI₃ to the TiO₂ ETM, which is considerably slower ($k_{e- \text{inject}} \sim 1.2 \times 10^7 \text{ s}^{-1}$) compared to hole injection from FAPbI₃ to Spiro-OMeTAD HTM ($k_{e- \text{inject}} > 5 \times 10^7 \text{ s}^{-1}$). Hence, this prevention of electron injection with excess MABF₄ addition could cause carrier accumulation at the heterointerface and might explain the observed QSS-PCE and EQE spectra of the PSCs with 5 mol% MABF₄.

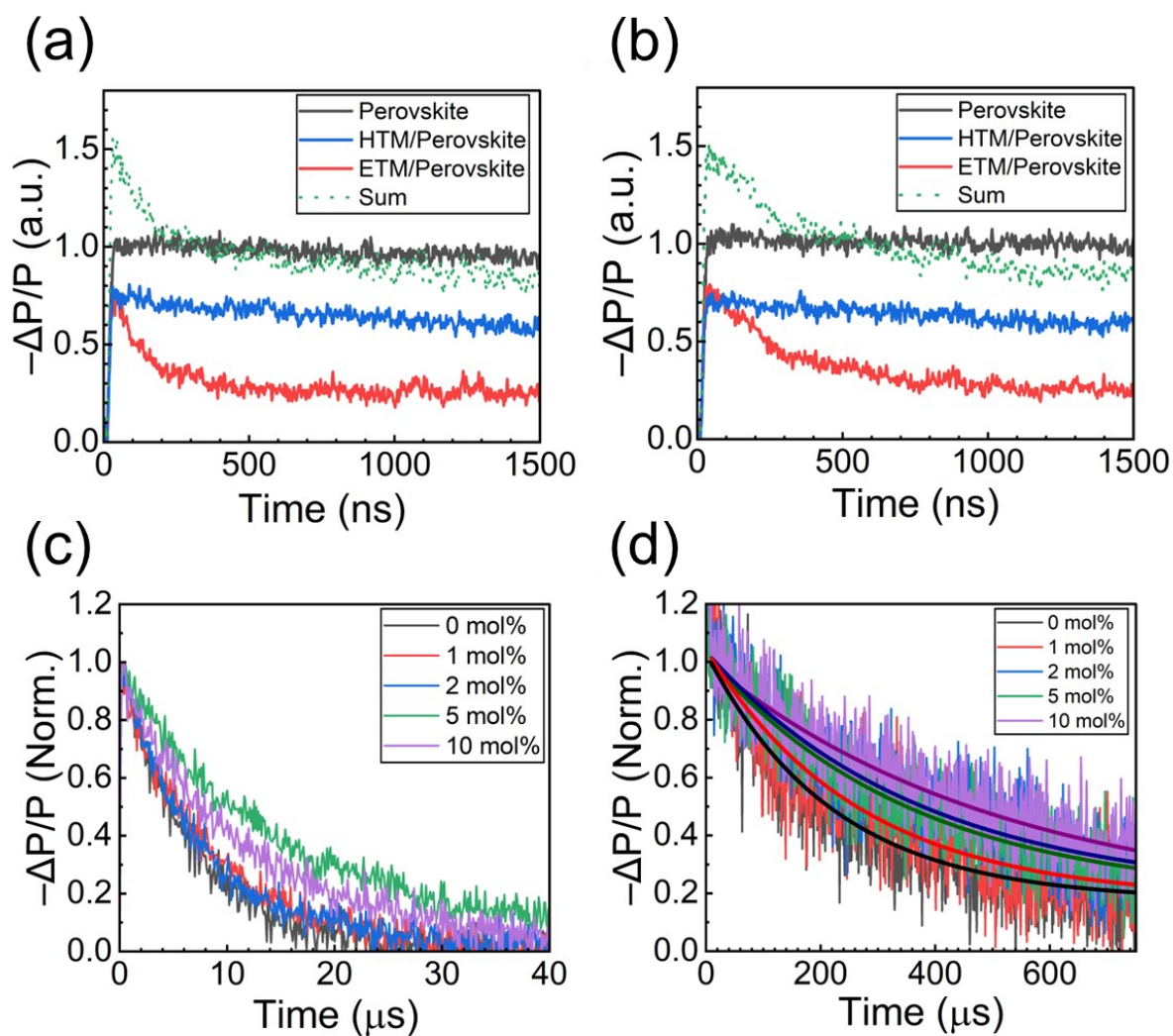


Figure 6. TRMC signal of the intensity of the monolayer and bilayer with a MABF₄ concentration of (a) 0 mol% and (b) 2 mol%. TRMC signal of the (c) HTM/FAPbI₃ and (d) FAPbI₃/ETM bilayers in a long range (short range: [Figure S10b](#)) with their corresponding fitting curves.

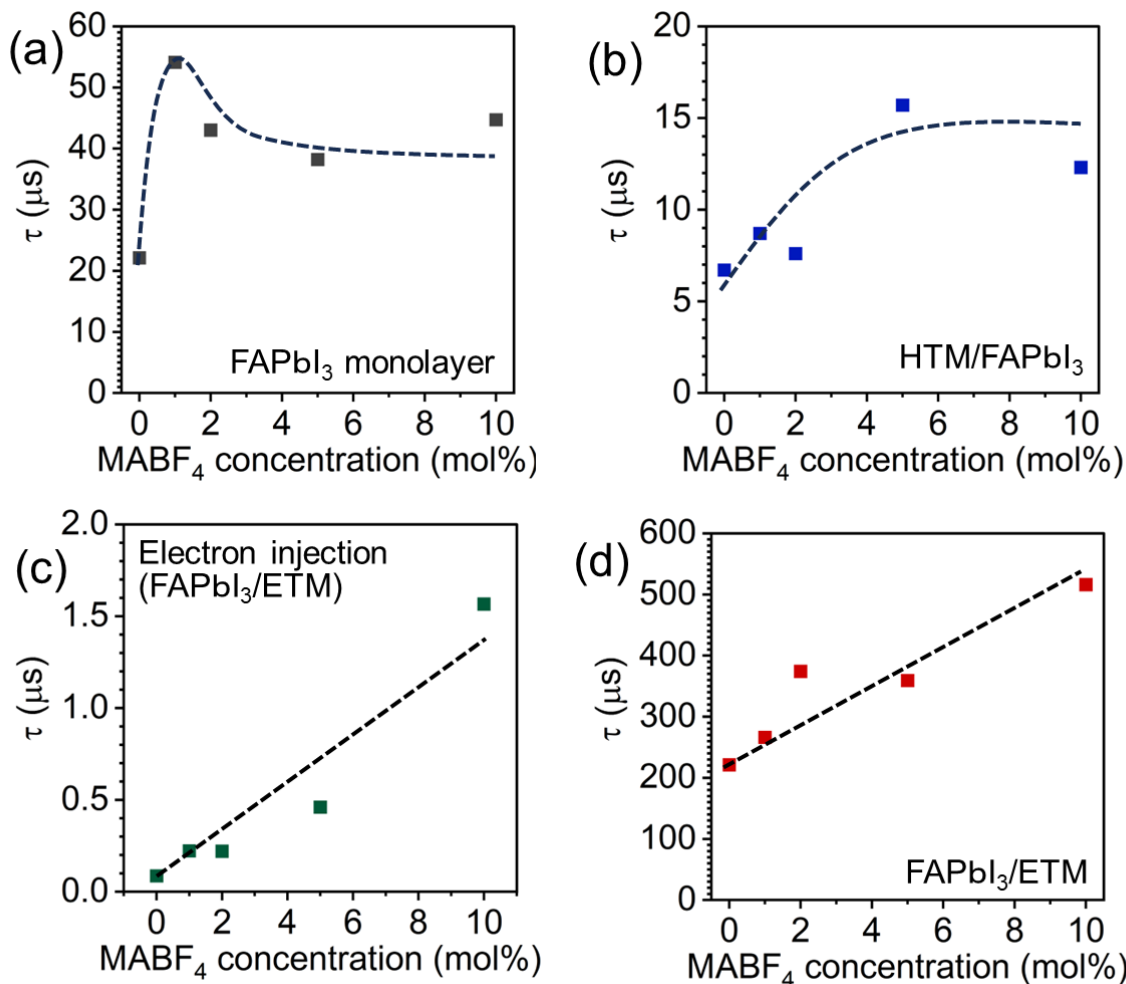


Figure 7. Averaged TRMC lifetimes of (a) FAPbI₃ monolayer samples, (b) HTM/FAPbI₃ bilayer samples, (c) FAPbI₃/ETM bilayer samples attributed to electron injection, (d) FAPbI₃/ETM bilayer samples after the electron injection

The addition of fluorinated components renders a material hydrophobic; therefore, the effects of MABF₄ addition on the PSC stability against humidity were investigated. Figure S12 shows the results of the stability tests conducted under humidity (303 K (30 °C), 50% relative humidity). Initially, the PCE of the sample without MABF₄ decreased to ~40% after 1500 h. In contrast, the addition of the optimal amount of MABF₄ resulted in considerable moisture resistance with over

85% of the initial PCE maintained after 1500 h. Previous studies on the BF_4^- additive reported its effect on the surface hydrophobicity of the perovskite layer and its stability against humidity. However, in our study, the contact-angle measurements of the perovskite surfaces performed using water droplets indicated that BF_4^- addition did not increase the hydrophobicity of the perovskite surfaces for both cases with and without OAI passivation (Figure S13). Meanwhile, the SIMS results indicated that species derived from BF_4^- anions were incorporated into the perovskite layer, although part of the BF_4^- anions was most likely decomposed. Fluorinated moieties are known for their hydrophobicity,⁶³⁻⁶⁵ thus, the BF_4^- anion species even partly decomposed render the perovskite bulk hydrophobic, and thereby, its stability against humidity was improved. Consequently, MABF_4 addition into FAPbI_3 is advantageous for improving the long-term stability of the devices against humidity owing to the presence of BF_4^- -derived species in the FAPbI_3 layer.

Conclusions

In this study, we revealed that although the combination of narrow-bandgap FAPbI_3 and BF_4^- -based additives, which can retain the narrow-bandgap, is promising, the effects of the additive on narrow-bandgap perovskites differ compared to those of wide-bandgap perovskites. Unlike conventional BF_4^- -based additives that primarily promote the crystal growth of wide-bandgap perovskites, the primary function of the MABF_4 additive in the FAPbI_3 photoabsorber is most likely the spontaneous modulation of the heterointerfaces between FAPbI_3 and the CTM. (Figure 1)

Although SEM images reveal that the addition of MABF_4 promoted FAPbI_3 crystal growth, the PV performance of the PSCs with the optimal amount of MABF_4 did not show V_{oc} enhancement, unlike in conventional BF_4^- addition. Instead, the proposed approach increased the

FF values and, thereby, enhanced the PCEs, which is consistent with the role of spontaneous heterointerface modulation.

Regarding the outer perovskite surface corresponding to the HTM/FAPbI₃ heterointerface, XPS measurements indicate that the defects of all perovskite composites (i.e., C, N, Pb, and I) decreased on the addition of MABF₄. For surface defect suppression using BF₄⁻-based additives, although the presence of the BF₄⁻ anion on the perovskite surface is vital for wide-bandgap perovskites, as shown by previous studies^{39, 41, 45}, the present results reveal that BF₄⁻ anion was absent on the FAPbI₃ surface during most of the duration for heating, suggesting a non-conventional defect suppression mechanism and provoking the importance of controlling FAPbI₃ nucleation.

Meanwhile, compositional depth analysis using SIMS revealed that the BF₄⁻ anions segregated at the FAPbI₃/ETM interface during deposition, although some of the BF₄⁻ anions were decomposed. TRMC measurements revealed the roles of the spontaneously modulated interfaces in addition to revealing the carrier mobility relationship of FAPbI₃: The carrier mobility ratio of FAPbI₃ between electrons (e⁻) and holes (h⁺) was 7:3, and the electron mobility in FAPbI₃ was substantially higher than that of the holes. Further, optimized MABF₄ addition effectively extended the carrier lifetimes in the presence of the heterointerfaces, and MABF₄ addition extended the hole lifetime of the FAPbI₃ photoabsorber in the presence of a FAPbI₃/TiO₂ heterointerface up to 516 ± 58 μs, which is extremely long. Thus, the improved heterointerfaces presumably contributed to the enhanced PV performance. (Figure 1) Furthermore, MABF₄ addition improved PSC stability against humidity presumably owing to the resulting hydrophobicity of the FAPbI₃ bulk upon the incorporation of BF₄⁻ species.

The promising combination of the narrow-bandgap FAPbI₃ and BF₄-based additives and identification of their roles in spontaneous heterointerface modulation will aid the further development of PSCs.

Supporting Information Available

Brief statement in nonsentence format listing the contents of the material supplied as Supporting Information

Author Contributions

Daisuke Kubota: Investigation, Resources, Formal analysis, Writing – original draft, Writing – review & editing, **Ryuzi Katoh:** Investigation, Formal analysis, Writing – review & editing, **Hiroyuki Kanda:** Writing – review & editing, **Hiroyuki Yaguchi:** Writing – review & editing, **Takuro N. Murakami:** Funding acquisition, Writing – review & editing, **Naoyuki Nishimura:** Supervision, Conceptualization, Project administration, Investigation, Resources, Formal analysis, Writing – review & editing.

Notes

There are no conflicts to declare.

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Abbreviations

CTM, carrier-transport material; ETM, electron transport material; EQE, external quantum efficiency; FA, formamidium; FTO, fluorine-doped tin oxide; FF, fill factor; MA, methylammonium; PCE, power conversion efficiency; PSC, perovskite solar cell; PV, photovoltaic; SIMS, secondary-ion mass spectrometry; TRMC, time-resolved microwave conductivity; XPS, X-ray photoelectron spectroscopy.

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